

1.Description

SS10N20MS, the N-channel Enhanced Power MOSFETs, is obtained by advanced double trench technology which reduce the conduction loss, improve switching performance and enhance the avalanche energy. This is suitable device for motor drivers and high speed switching applications.

KEY CHARACTERISTICS

Parameter	Value	Unit
V _{DSS}	200	V
I _D	135	A
R _{DS(on)} .typ	9.5	mΩ

FEATURES

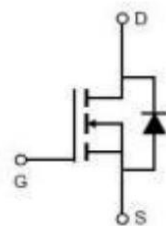
- Fast Switching
- Low On-Resistance ($R_{DS(on)} \leq 10.5\text{m}\Omega$)
- Low Gate Charge
- Low Reverse transfer capacitances
- High avalanche ruggedness
- RoHS product

APPLICATIONS

- Switching applications
- Motor drivers
- BMS
- Synchronous rectification

ORDERING INFORMATION

Ordering Codes	Package	Product Code	Packing
SS10N20MS	TO-263	SS10N20MS	Reel



TO-263

